

## **Further Comments of the HL-LHC Experiments concerning the LGAD Runs planned for 2018 at HPK.**

Motivated by the highly successful meeting on Dec 19, 2018 in Hamamatsu, Japan, the representatives of ATLAS and CMS would like to continue the collaboration with HPK engineers on the new runs planned for 2018.

### **Important date for ATLAS-HGTD and CMS-ETL: Technical Design Report in late Summer 2018**

The following fact needs to be emphasized again: for both experiments, the most important milestone is the submission of the Technical Design Report (TDR) in in the 3<sup>rd</sup> Quarter 2018, i.e. before the end of September 2018. For that date, we have to prove that LGADs can be produced reliably and with high yield in arrays of multiple pads, and the most important technical solutions need to be understood.

To achieve this goal, a production of large sensors has been planned at the Dec 19<sup>th</sup> meeting.

### **Spring 2018: production of full wafers containing large sensors for ATLAS and CMS (LargeSensor\_HP K).**

Both ATLAS and CMS need to prove the existence of large sensors (~ 100 pads), which can operate reliably when new and irradiated, with good gain uniformity.

For this reason, a production of large sensors (LargeSensor\_HP K) is needed, where reliability and gain uniformity before and after irradiation are the two most essential parameters. We assume that many of the design details will be similar to those of the proven "Sample 50D" from the Nov 2016 delivery, with the exception of the pad size.

In Appendix A.1 and A.2 the top-level sensors layout for LargeSensor\_HP K from ATLAS and CMS are presented.

We would like to receive soon feedback if there are any parts of our request which would prevent HPK from shipping the devices in or before June 2018 so that they can be irradiated and tested before the TDR. In that case we would like to propose a phone conference on this subject so that we can adjust the scope of our request.

### **Spring 2018: Sensor production for technology development of LGAD by HPK (TechSensor\_HP K).**

We are looking forward to further optimization of the LGAD technology by HPK in early 2018. For this reason, a production in early spring 2018 will be manufactured (TechSensor\_HP K). Based on our measurements, we have recommended in this production studies with variations of important parameters so that they can be optimized in the final prototype next year: reduced inter-pad distance, reduced edge space, two thicknesses (50 & 35  $\mu\text{m}$ ), and the optimization of the doping concentration and depth of the p-type multiplication layer.

We expect that we will be doing most of the testing of the different variations including radiation testing, for which we believe we have developed a methodology tailored to the needs of the experiments. Testing includes I-V and C-V curves, charge collection, and timing studies.

The availability of 20-30 parts of each type made the previous studies of HPK a success, and therefore we recommend planning for this number of devices in each variation.

We would like to recommend that both the CMS basic cell with an external size (“pitch”) of  $1 \times 3 \text{ mm}^2$  and the ATLAS basic cell with an external size (“pitch”) of  $1.3 \times 1.3 \text{ mm}^2$  are proto-typed.

We are motivated to have a phone conference with HPK engineers to discuss and review proposed plans.

### **Path to the ATLAS and CMS TDR: LargeSensor\_HP K + TechSensor\_HP K**

We understand that LargeSensor\_HP K might not benefit from the technical developments studied in TechSensor\_HP K, however this is not necessary for the ATLAS and CMS TDR. The combination of the technical development obtained in TechSensor\_HP K with the uniformity studies of LargeSensor\_HP K will provide a solid base for the TDR.

### **Schedule of future (2018-2022) ATLAS and CMS LGAD productions.**

In the following, we would like to provide HPK the schedule for LGAD productions at ATLAS and CMS so that a long term R&D activity can be established.

#### **ATLAS Schedule for HGTD sensor production:**

##### **Q2-3 2018: Production of TechSensor\_HP K and LargeSensor\_HP K**

- Study of technical solutions (edge, fill factor, doping)
- Sensors with 225 pads, and many test structures

##### **Q3 2018: TDR**

##### **2019 - 2020: Sensor2\_HGTD production**

- Large sensors, implementation of all the technical solutions

##### **2021: Sensor3\_HGTD production**

- Pre-Production of sensors with full HGTD specifications

##### **2022 - 2023: Sensor4\_HGTD production**

- Production of sensors for HGTD construction

## **CMS Schedule for ETL sensor production:**

### **Q2-3 2018: Production of TechSensor\_HP K and LargeSensor\_HP K**

Study of technical solutions (edge, fill factor, dopings)

→ Sensors with 96 pads (one CMS read-out chip), and many test structures

### **Q3 2018: TDR**

### **2019 - 2020: Sensor2\_CMS production**

→ Large sensors, implementation of all the technical solutions

### **2021: Sensor3\_CMS production**

→ Pre-Production of sensors with full CMS specifications

### **2022 -2023: Sensor4\_CMS production**

→ Production of sensors for CMS ETL construction

# Appendix A

## Top level wafer definition of CMS/ATLAS LGAD submission (approximate numbers)

- Wafer active thickness: 50  $\mu\text{m}$  (baseline) and 35  $\mu\text{m}$  (option)

### A.1 ATLAS HGTD

Basic cell (outside dimension) 1.3x1.3 mm<sup>2</sup>

Single pad LGAD: ~ 150

Single pad PIN: ~ 30

Arrays 2x2: ~ 25 per inter-pad distance (3 distances)

3x3: ~ 7 per inter-pad distance (3 distances)

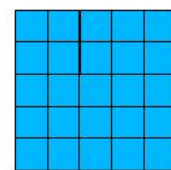
5x5: ~ 30 devices, safe inter-pad distance, UBM

15x15 ~ 8 devices, safe inter-pad distance, UBM

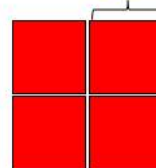
## ATLAS HGTD Sensor List

- Wafer active thickness: 50  $\mu\text{m}$  (baseline) and 35  $\mu\text{m}$  (option)
- Pad size always 1.3x1.3 mm<sup>2</sup>
- Structures (LGAD if not noted otherwise)
  - LGAD single pad, PIN single pad
  - Arrays of 2x2 and 3x3 pads
    - Inter-pad gap variations: 30, 50, 70  $\mu\text{m}$ ? (CNM standard 64  $\mu\text{m}$  physical)
    - Slim edge variations: 100, 200, 300  $\mu\text{m}$ ? -> optimized edge design (GR etc.) for each
    - Large passivation openings for wire-bonding/probe needles
  - Arrays of 5x5 pads
    - Compatible to next version of HGTD readout chip (ALTIROC1, mid 2018)
    - Standard inter-pad gap (50-100  $\mu\text{m}$ ) and standard edge (300-500  $\mu\text{m}$ ) (conservative values)
    - 2 different passivation openings or alternatively biasing structures to allow both UBM/bump-bonding and probing/wirebonding
  - Large arrays of 15x15 pads (single-chips) and 30x15 pads (double-chips)
    - Compatible to final HGTD readout chip (~2019)
    - Designed as single-chip sensors, but arranged to allow yield-evaluation and dicing as pseudo-doubles and quads for module proto-typing
    - Standard inter-pad gap (50-100  $\mu\text{m}$ ) and standard edge (300-500  $\mu\text{m}$ ) (conservative values)
    - 2 different passivation openings or alternatively biasing structures to allow both UBM/bump-bonding and probing/wirebonding

1.3 mm

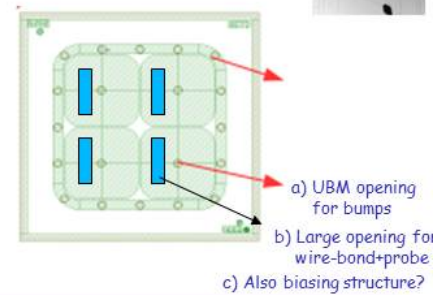
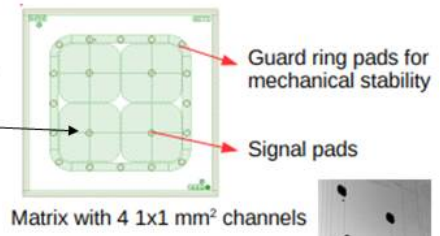
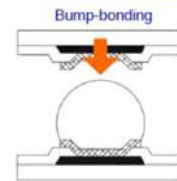


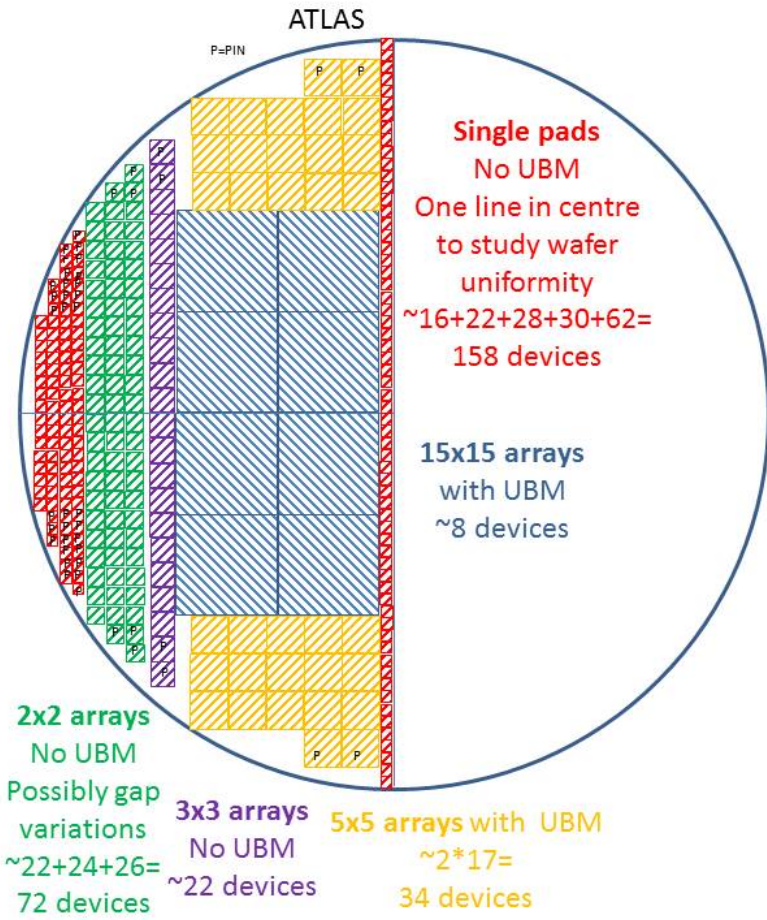
15 pads



# Bump-Bonding

- Need to bump-bond sensor to readout chip
- Need Under-Bump-Metalization (UBM)
  - Provided by vendor?
  - Which process? Is a mask used to protect other metal not foreseen for UBM?
    - Do structures for UBM need to be on one part of the wafer?
- HGTD bump-bonding tests so far
  - On CNM HGTD run (2x2 arrays for first version of readout chip: ALTIROC0)
  - Passivation opening of 90  $\mu\text{m}$  diameters
  - Electro-less UBM in house by CNM
  - Bump-deposition of 80  $\mu\text{m}$  diameter bumps and flip-chipping
  - Good results: hybrid works and delivers signal; good mechanical stability
- How do we assure probing (IV) and sensor selection on wafer?
  - Several options possible
    1. Implement 2 passivation openings on same pad: both small opening for UBM and large opening for probing/wire-bonding  
-> allows to probe IV of large sensors with probe card
    2. Temporary metal to shorten all pads
    3. Biasing structures like for pixels (e.g. punch-through or poly-Si)





## 6" LGAD wafer layout proposal (sketch)

- Shared between ATLAS/CMS (half-half)
- **ATLAS pad:  $1.3 \times 1.3 \text{ mm}^2$  active area**
- Some PINs for each structure
- Here not completely closely packed/well aligned (just a sketch) and each sensor has conservative  $500 \mu\text{m}$  inactive width at each edge (incl. GR, margin, cut line) -> slightly higher density possible
- Typically arrays have safe standard inter-pad gap like 50D
- 2x2 arrays can have variations
  - Gap of e.g. 30, 50, 70  $\mu\text{m}$  to optimise fill factor
  - Slim edge (100, 200, 300  $\mu\text{m}$ )
- Large sensors (5x5, 15x15)
  - UBM (90  $\mu\text{m}$  passivation hole in centre)
  - Additional structures for probing (larger openings for needles/wire bonds, maybe biasing structure)
  - 8 15x15 single-chip sensors
    - Designed as single-chip sensors, but arranged to allow yield-evaluation and dicing as pseudo-doubles and quads for module proto-typing

## A.2 CMS ETL

Basic cell (outside dimension)  $1.0 \times 3.0 \text{ mm}^2$

Single pad LGAD: ~ 100

Single pad PIN: ~ 20

Arrays 2x2: ~ 20

2x2 PIN: ~ 2

3x3: ~ 15 per inter-pad distance

4x4: ~ 16 devices,

4x24 ~ 16 devices,

3x3 ( $1 \times 2 \text{ mm}^2$ ): ~ 12



## CMS wish list for 2018 production

### General remarks

- Pad size always  $1 \times 3 \text{ mm}^2$  unless otherwise stated
- LGADs unless otherwise stated
- All pads to be wire-bonded

### List of structures

- LGAD and PIN single pads
- 2x2 arrays
- 3x3 arrays
- 3x3 arrays with  $1 \times 2 \text{ mm}^2$  pad size
- 4x4 arrays
- **CMS small prototype:** 4x24 arrays (96 pads). This matches the CMS ROC size.

